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May 2014

FGH40T100SMD 1000 V, 40 A Field Stop Trench IGBT

Features

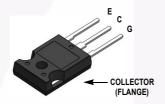
- · High Current Capability
- Low Saturation Voltage: $V_{CE(sat)}$ = 1.9 V(Typ.) @ I_C = 40 A
- · High Input Impedance
- · Fast Switching
- RoHS Compliant

Applications

· UPS, welder, PFC

General Description

Using innovative field stop trench IGBT technology, Fairchild's new series of field stop trench IGBTs offer the optimum performance for hard switching application such as UPS, welder and PFC applications.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit	
V _{CES}	Collector to Emitter Voltage		1000	V	
V_{GES}	Gate to Emitter Voltage		± 25	V	
* GES	Transient Gate to Emitter Voltage		± 30	V	
I _C	Collector Current	$@T_C = 25^{\circ}C$	80	Α	
'C	Collector Current	@ T _C = 100°C	40	Α	
I _{CM (1)}	Pulsed Collector Current @ T _C = 25°C		120	Α	
I _F	Diode Forward Current	@ T _C = 25°C	80	A	
	Diode Forward Current	@ T _C = 100°C	40	A	
I _{FM (1)}	Pulsed Diode Forward Current	@ T _C = 25°C	120	Α	
P _D	Maximum Power Dissipation	@ T _C = 25°C	333	W	
r D	Maximum Power Dissipation	@ T _C = 100°C	166	W	
T _J	Operating Junction Temperature		-55 to +175	°C	
T _{stg}	Storage Temperature Range		-55 to +175	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

Notes

Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	-	0.45	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	-	0.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGH40T100SMD	FGH40T100SMD	TO-247 A03	-	-	30ea
FGH40T100SMD	FGH40T100SMD_F155	TO-247 G03	-	-	30ea

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	V _{GE} = 0 V, I _C = 1 mA	1000	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0 V, I _C = 250 uA	-	0.6	-	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0 V	-	-	1000	μΑ
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}$, $V_{CE} = 0$ V	/-	-	±500	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	I _C = 250 uA, V _{CE} = V _{GE}	4.2	5.3	6.5	V
		I _C = 40 A, V _{GE} = 15 V	-	1.9	2.3	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 40 A, V _{GE} = 15 V, T _C = 175°C	-	2.4	-	٧
Dynamic C	haracteristics					
C _{ies}	Input Capacitance		-	3980	5295	pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz	-	124	165	pF
C _{res}	Reverse Transfer Capacitance	-1 - 1 1/11 12	-	76	115	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time		-	29	38	ns
t _r	Rise Time	V _{CC} = 600 V, I _C = 40 A,	-	42	55	ns
t _{d(off)}	Turn-Off Delay Time		-	285	371	ns
t _f	Fall Time	$R_G = 10 \Omega$, $V_{GE} = 15 V$,	-	23	30	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 25°C	-	2.35	3.1	mJ
E _{off}	Turn-Off Switching Loss		-/	1.15	1.5	mJ
E _{ts}	Total Switching Loss		-	3.5	4.6	mJ
t _{d(on)}	Turn-On Delay Time		-	27	36	ns
t _r	Rise Time		-	49	64	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 40 \text{ A},$	-	285	371	ns
t _f	Fall Time	$R_G = 10 \Omega$, $V_{GE} = 15 V$,	-	20	26	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 175°C	-	4.4	5.7	mJ
E _{off}	Turn-Off Switching Loss		-	1.9	2.5	mJ
E _{ts}	Total Switching Loss		-	6.3	8.2	mJ
Qg	Total Gate Charge		-	265	398	nC
Q _{ge}	Gate to Emitter Charge	V _{CE} = 600 V, I _C = 40 A, V _{GE} = 15 V	-	32	48	nC
Q _{gc}	Gate to Collector Charge] GE 10 V	-	135	203	nC

Electrical Characteristics of Diode T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
V _{FM}	Diode Forward Voltage	I _F = 40 A	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	3.4	4.4	V
			T _C = 175°C	-	2.6	-	
t	t _{rr} Diode Reverse Recovery Time		$T_C = 25^{\circ}C$	-	60	78	ns
In Diode Reverse Recovery Time	I _E =40 A, dI _E /dt = 200 A/μs	$T_{\rm C} = 175^{\rm o}{\rm C}$	-	256	-		
Q.,,	Q _{rr} Diode Reverse Recovery Charge		$T_C = 25^{\circ}C$	-	185	260	nC
~11			T _C = 175°C	-	1512	-	

Figure 1. Typical Output Characteristics

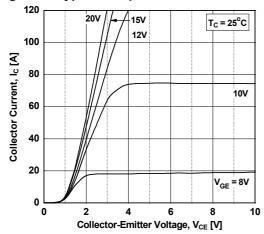


Figure 3. Typical Saturation Voltage Characteristics

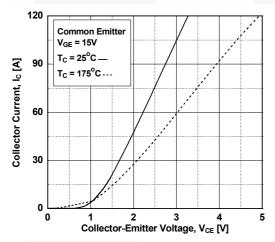


Figure 5. Saturation Voltage vs. V_{GE}

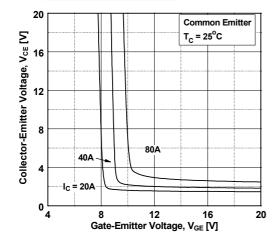


Figure 2. Typical Output Characteristics

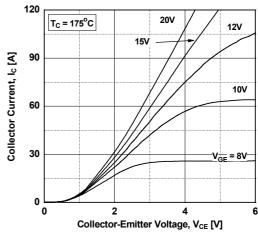


Figure 4. Saturation Voltage vs. Case
Temperature at Variant Current Level

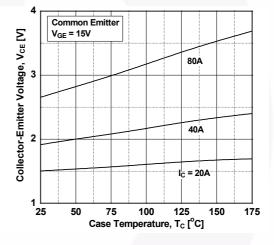


Figure 6. Saturation Voltage vs. V_{GE}

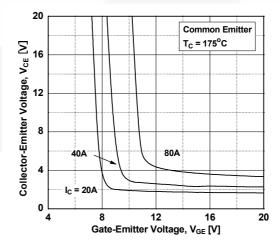


Figure 7. Capacitance Characteristics

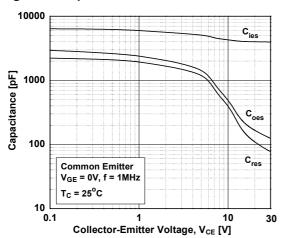


Figure 9. Turn-on Characteristics vs. Gate Resistance

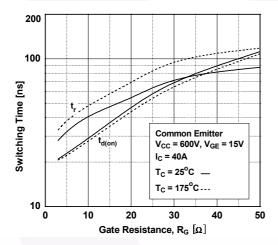


Figure 11. Switching Loss vs.

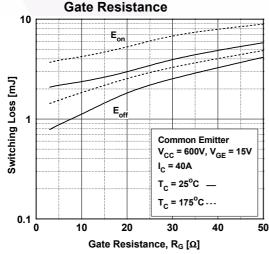


Figure 8. Gate charge Characteristics

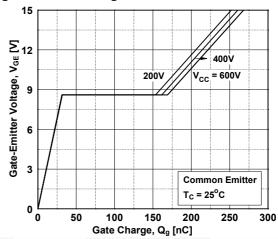


Figure 10. Turn-off Characteristics vs.
Gate Resistance

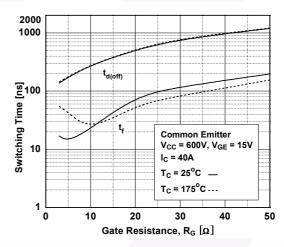


Figure 12. Turn-on Characteristics vs. Collector Current

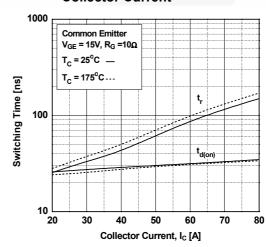


Figure 13. Turn-off Characteristics vs. Collector Current

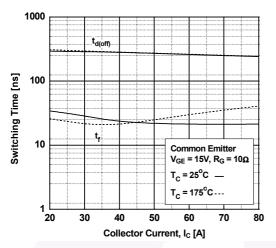


Figure 15. Load Current Vs. Frequence

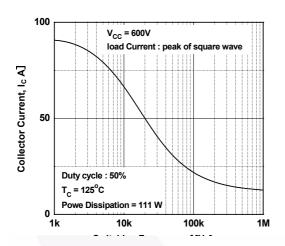


Figure 17. Forward Characteristics

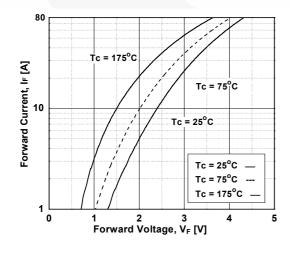


Figure 14. Switching Loss vs.
Collector Current

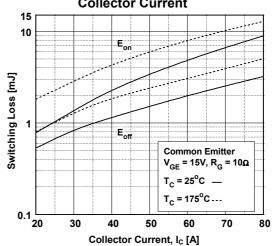


Figure 16. SOA Characteristics

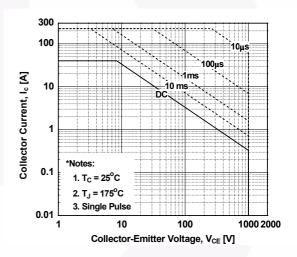


Figure 18. Reverse Recovery Current

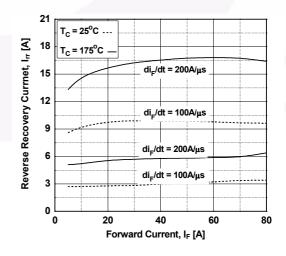


Figure 19. Reverse Recovery Time

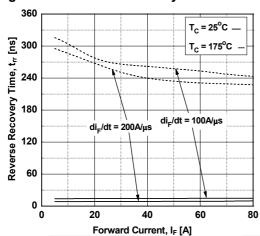


Figure 20. Stored Charge

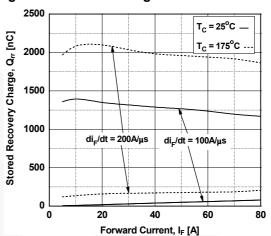


Figure 21. Transient Thermal Impedance of IGBT

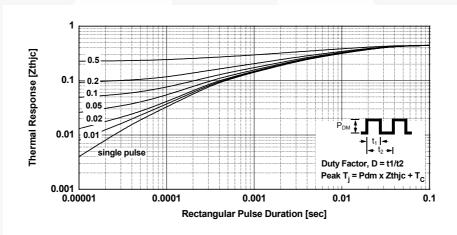
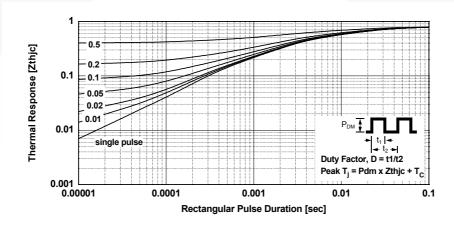


Figure 22. Transient Thermal Impedance of Diode



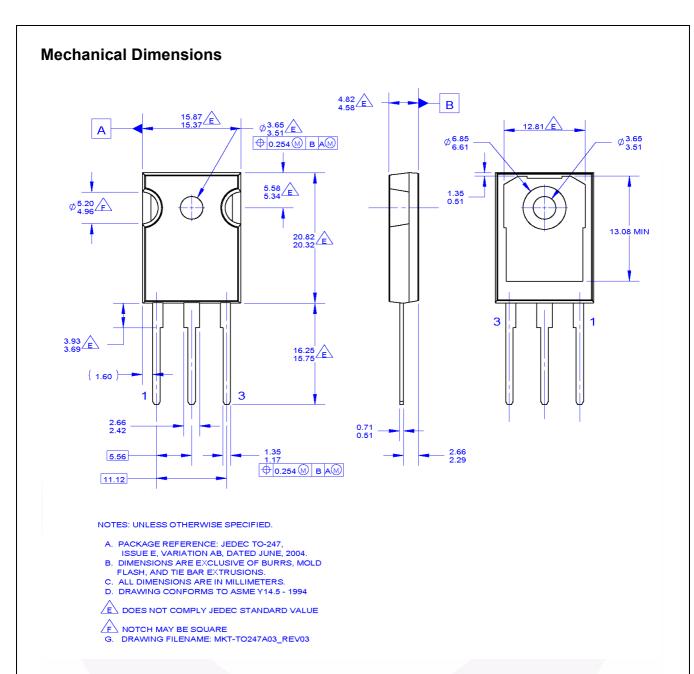


Figure 23. TO-247, MOLDED, 3 LEAD, JEDEC VARIATION AB (Active)

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Dimensions in Millimeters

Mechanical Dimensions

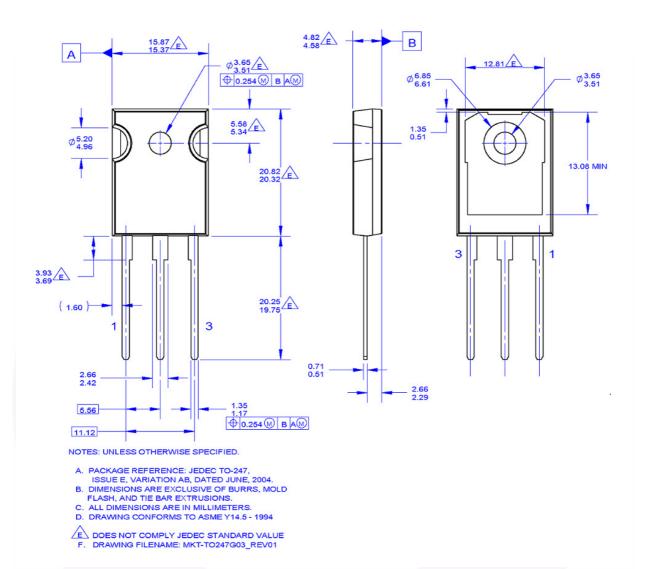


Figure 23. TO-247 3L - TO-247, MOLDED, 3 LEADS, JEDEC AB LONG LEADS

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